

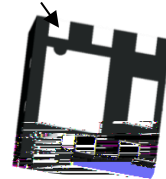
### Product Summary

The ZM220N03L combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .



Trench technology

$R_{DS(ON)}$  to minimize conductive loss  
 for fast switching



DC/DC Converters in Computing, Servers  
 Isolated DC/DC Converters in Telecom and Industrial

	REEL TAPE
	3000

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	12	V
Continuous Drain Current	$I_D@T_C=25$	5	A
	$I_D@T_C=75$	3.8	A
	$I_D@T_C=100$	3	A
Pulsed Drain Current	$I_{DM}$	15	A
Total Power Dissipation	$P_D@T_C=25$	18	W
Total Power Dissipation	$P_D@T_A=25$	0.9	W
Operating Junction Temperature	$T_J$	-55 to 150	
Storage Temperature	$T_{STG}$	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	$E_{AS}$	5	mJ



Fig.1 Gate-Charge Characteristics

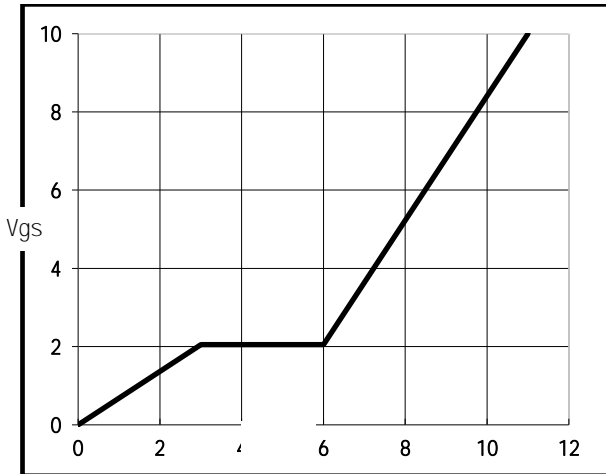


Fig.2 Capacitance Characteristics

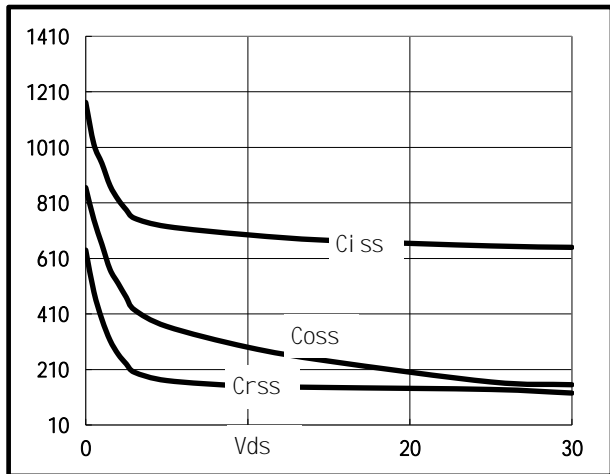


Fig.3 Power Dissipation Derating Curve

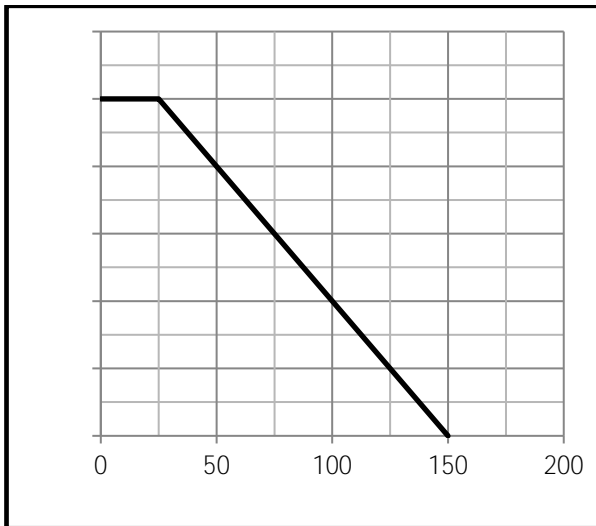


Fig.4 Typical output Characteristics

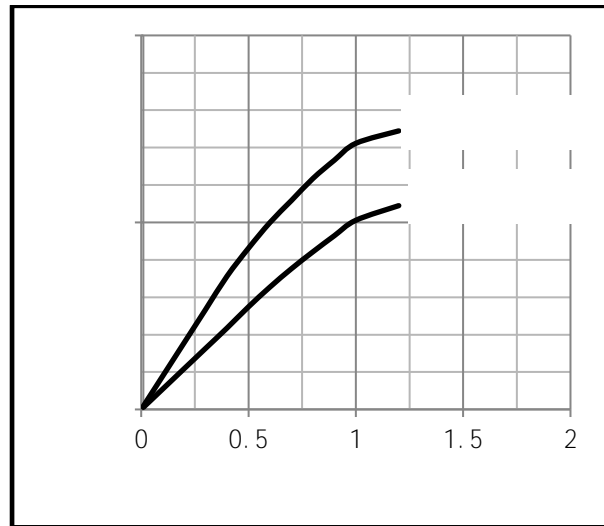


Fig.5 Threshold Voltage V.S Junction Temperature

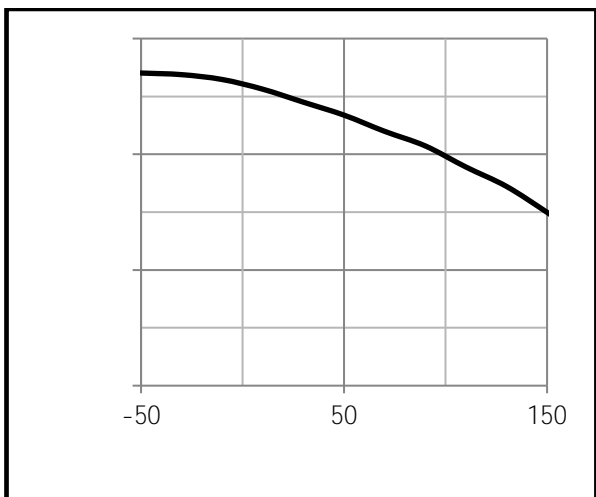
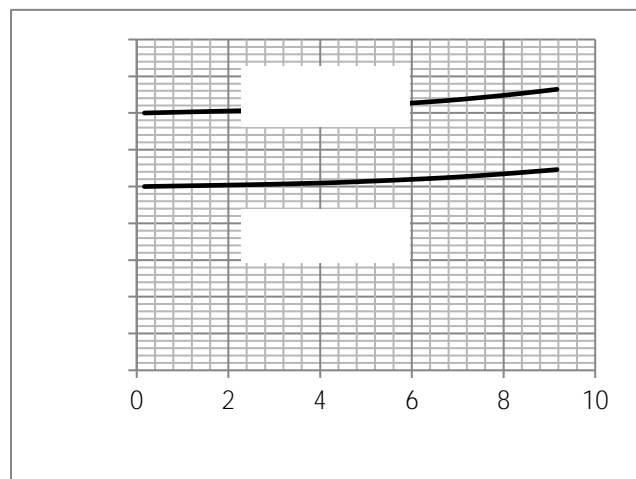


Fig.6 Resistance V.S Drain Current

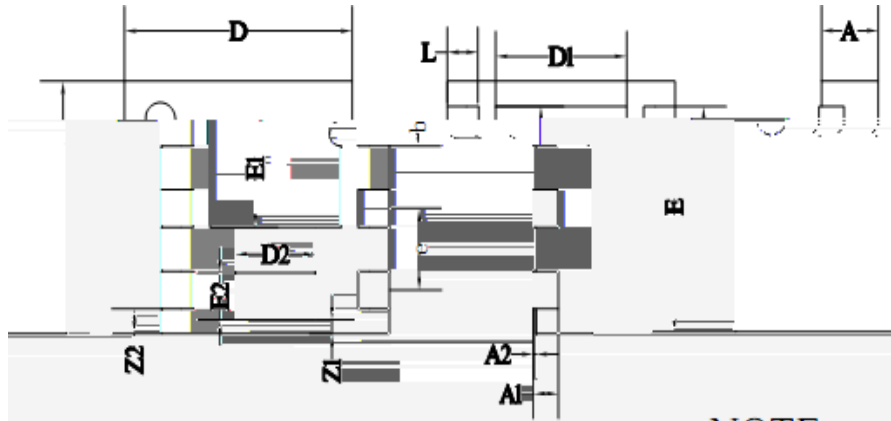






(DFN2\*2)

Unit mm



NOTE:

All dimensions are in mm

NOV	MAX	MIN
200	205	D
200	205	E
115	120	D1
125	130	E1
0.25	0.30	Z1
0.25	0.30	Z2
0.30	0.35	A1
0.30	0.35	A2
0.45	0.50	A
0.25	0.30	L
0.25	0.30	D2